

Maximum Ratings (@T_A = +25°C unless otherwise specified.)

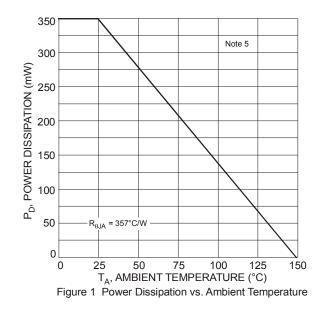
Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	50	V
Collector-Emitter Voltage	V _{CEO}	45	V
Emitter-Base Voltage	V _{EBO}	6	V
Collector Current	Ιc	100	mA

Thermal Characteristics – Total Device (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5) Total Device	PD	350	mW
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	357	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-65 to +150	°C

Note: 5. For a device surface mounted on minimum recommended pad layout FR-4 PCB with single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

Thermal Characteristics – Total Device

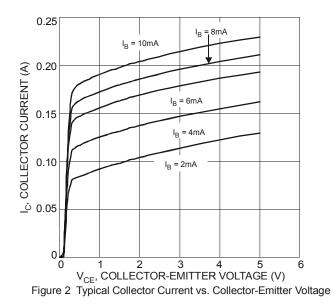


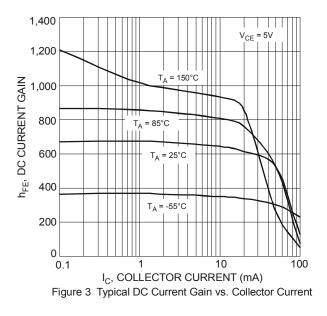


Electrical Characteristics (@T_A = +25°C unless otherwise specified.)

Characteristic (Note 6)	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	50	_	_	V	I _C = 100μA, I _B = 0
Collector-Emitter Breakdown Voltage	BV _{CEO}	45	_	_	V	$I_{\rm C} = 10 {\rm mA}, I_{\rm B} = 0$
Emitter-Base Breakdown Voltage	BV _{EBO}	6	_	_	V	I _E = 100μA, I _C = 0
DC Current Gain	h _{FE}	420	650	800	—	V _{CE} = 5.0V, I _C = 2.0mA
Collector-Emitter Saturation Voltage	V _{CE(sat)}	_	55 130	250 600	mV	I_{C} = 10mA, I_{B} = 0.5mA I_{C} = 100mA, I_{B} = 5.0mA
Base-Emitter Saturation Voltage	V _{BE(sat)}	_	700 900	_	mV	I_{C} = 10mA, I_{B} = 0.5mA I_{C} = 100mA, I_{B} = 5.0mA
Base-Emitter Voltage	V _{BE(on)}	580 —	660 —	700 770	mV	V_{CE} = 5.0V, I _C = 2.0mA V_{CE} = 5.0V, I _C = 10mA
Collector-Cutoff Current	I _{CES}			15	nA	V _{CE} = 50V
Collector-Cutoff Current	I _{СВО}	_	_	15 5	nA μA	V _{CB} = 30V V _{CB} = 30V, T _A = +150°C
Gain Bandwidth Product	f _T	100	_	_	MHz	V _{CE} = 5.0V, I _C = 10mA, f = 100MHz
Collector-Base Capacitance	C _{CBO}	_	2.0	_	pF	V _{CB} = 10V, f = 1.0MHz

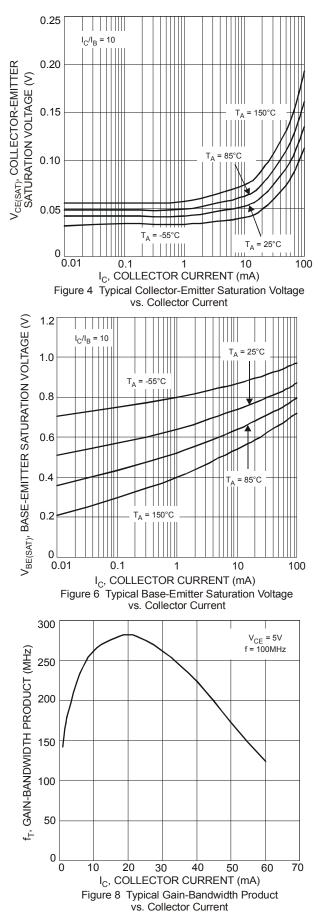
Note: 6. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.

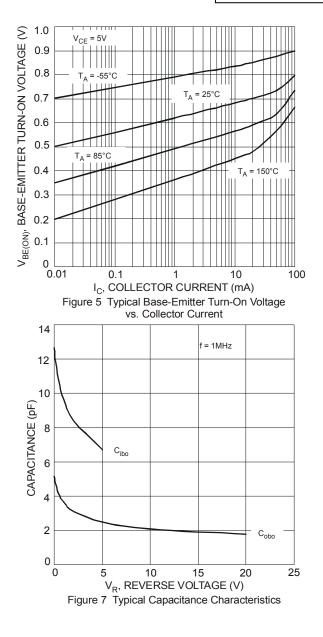








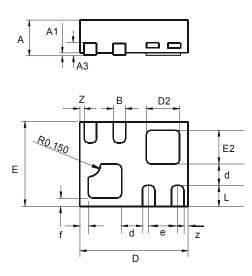






Package Outline Dimensions

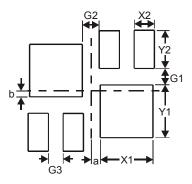
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



X2-DFN1310-6				
Dim	Min	Max	Тур	
Α		0.40		
A1	0	0.05	0.02	
A3		_	0.13	
b	0.10	0.20	0.15	
D	1.25	1.38	1.30	
d		_	0.25	
D2	0.30	0.50	0.40	
ш	0.95	1.075	1.00	
e			0.35	
E2	0.30	0.50	0.40	
f	_		0.10	
L	0.20	0.30	0.25	
Z			0.05	
All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)	
G1	0.16	
G2	0.17	
G3	0.15	
X1	0.52	
X2	0.20	
Y1	0.52	
Y2	0.375	
а	0.09	
b	0.06	



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